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Kim et al.

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(54) **DISPLAY DEVICE AND METHOD FOR
MANUFACTURING THE SAME**

(75) Inventors: **Sang Dae Kim**, Daegu (KR); **Jung
Hwan Lee**, Daegu (KR); **Ho Won Choi**,
Gumi-si (KR)

(73) Assignee: **LG Electronics Inc.**, Seoul (KR)

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U.S.C. 154(b) by 789 days.

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(30) **Foreign Application Priority Data**

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H05B 33/22 (2006.01)

(52) **U.S. Cl.** **313/509**; 445/24

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438/34, 82; 257/40, 72, 98–100, 642–643,
257/759; 427/58, 64, 66, 532–535, 539;
445/24–25

See application file for complete search history.

(56) **References Cited**

U.S. PATENT DOCUMENTS

5,958,610 A * 9/1999 Yonekawa et al. 428/690

7,388,225 B2 * 6/2008 Fukuhara et al. 257/59
2001/0049153 A1 * 12/2001 Tanaka 438/29
2004/0027064 A1 2/2004 Tanabe et al.
2005/0007016 A1 1/2005 Mori
2005/0067952 A1 3/2005 Fechter et al.
2005/0093439 A1 * 5/2005 Harada et al. 313/506
2005/0212410 A1 * 9/2005 Su 313/504
2006/0043888 A1 * 3/2006 Nakagawa et al. 313/506
2006/0082285 A1 * 4/2006 Wu et al. 313/503
2006/0163565 A1 * 7/2006 Park et al. 257/40
2006/0181199 A1 8/2006 Lee et al.
2006/0208632 A1 * 9/2006 Kang 313/503

FOREIGN PATENT DOCUMENTS

EP 0 493 975 7/1992

(Continued)

OTHER PUBLICATIONS

European Search Report dated Oct. 5, 2007.

(Continued)

Primary Examiner—Nimeshkumar D Patel

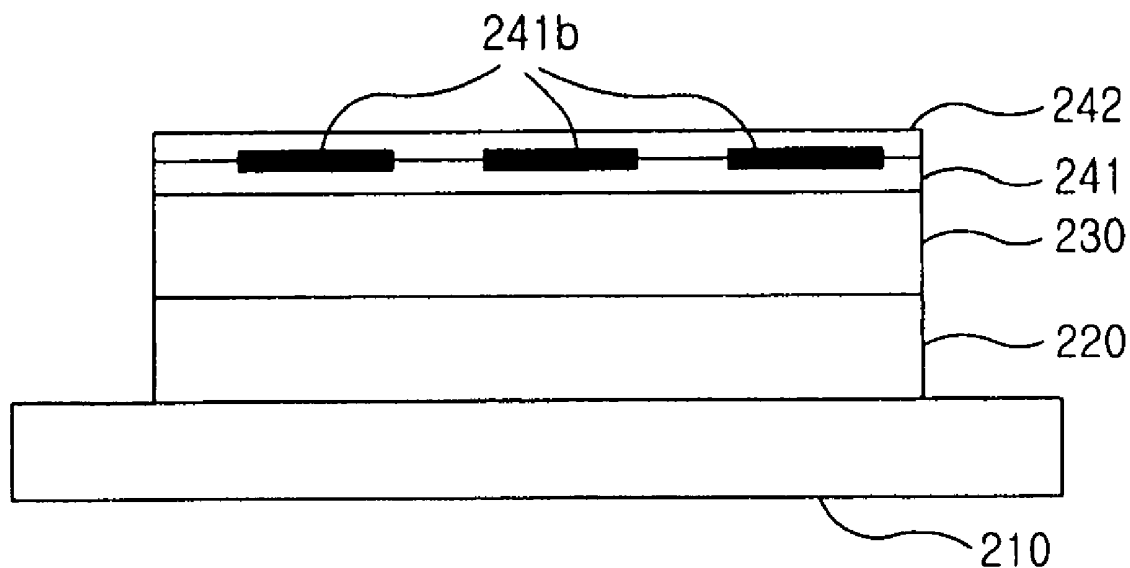
Assistant Examiner—Donald L Raleigh

(74) *Attorney, Agent, or Firm*—KED & Associates, LLP

(57) **ABSTRACT**

An electroluminescent device may be provided that includes a substrate, a first electrode provided on the substrate, a light emitting layer provided on the first electrode, and a first metal layer provided on the light emitting layer. An oxide layer may also be provided at an interface of the first metal layer and a conductive particle. Other embodiments as described herein may also be provided.

23 Claims, 12 Drawing Sheets



FOREIGN PATENT DOCUMENTS

JP	2001-189191	7/2001
JP	2004-119029	4/2004
JP	2005-044799	2/2005
JP	2005-50706	2/2005
KR	10-2005-0031989	4/2005
KR	10-2006-0091648	8/2006
KR	10-2007-0025253	3/2007

WO WO 01/15496 3/2001

OTHER PUBLICATIONS

Korean Office Action dated Jul. 7, 2007.

Chinese Office Action dated Feb. 6, 2009 and English language translation.

Korean Notice of Allowance dated Jun. 25, 2007 and English-language translation.

* cited by examiner

FIG. 1

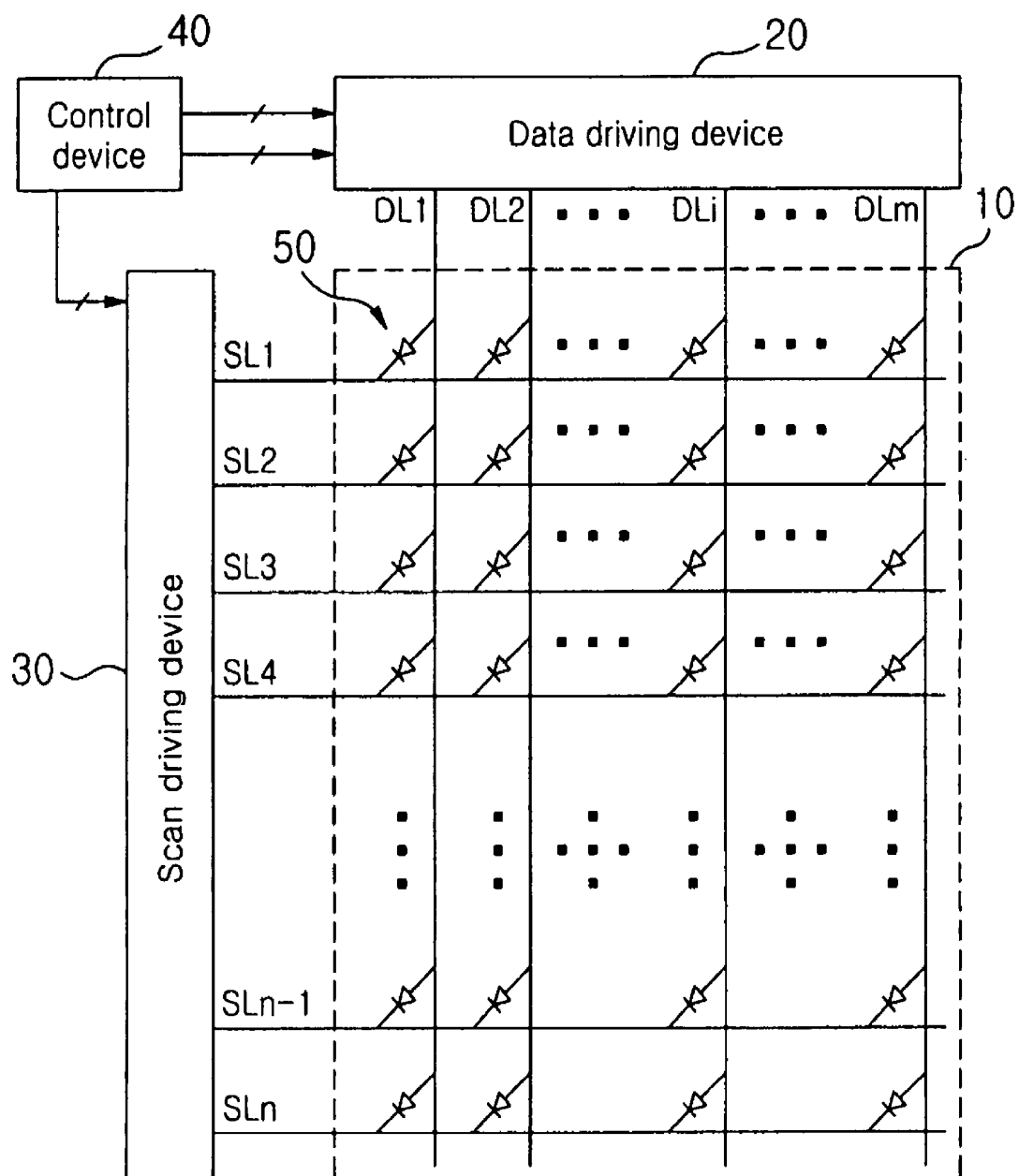


FIG. 2

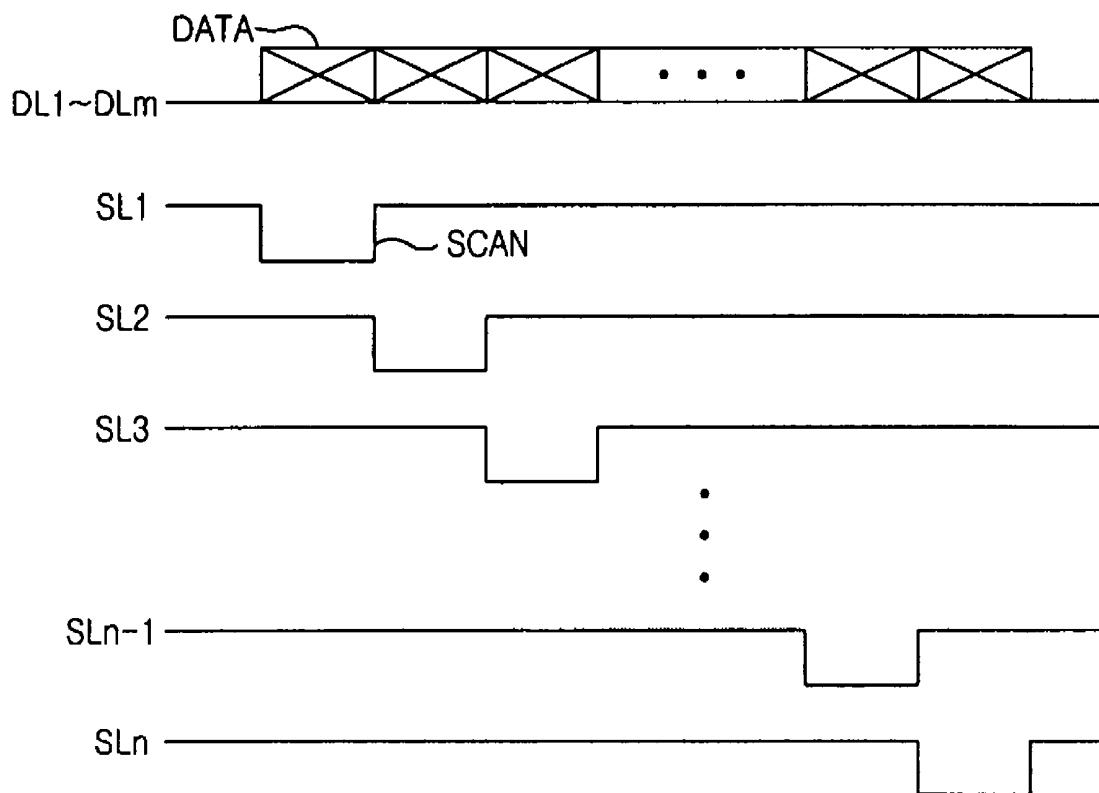


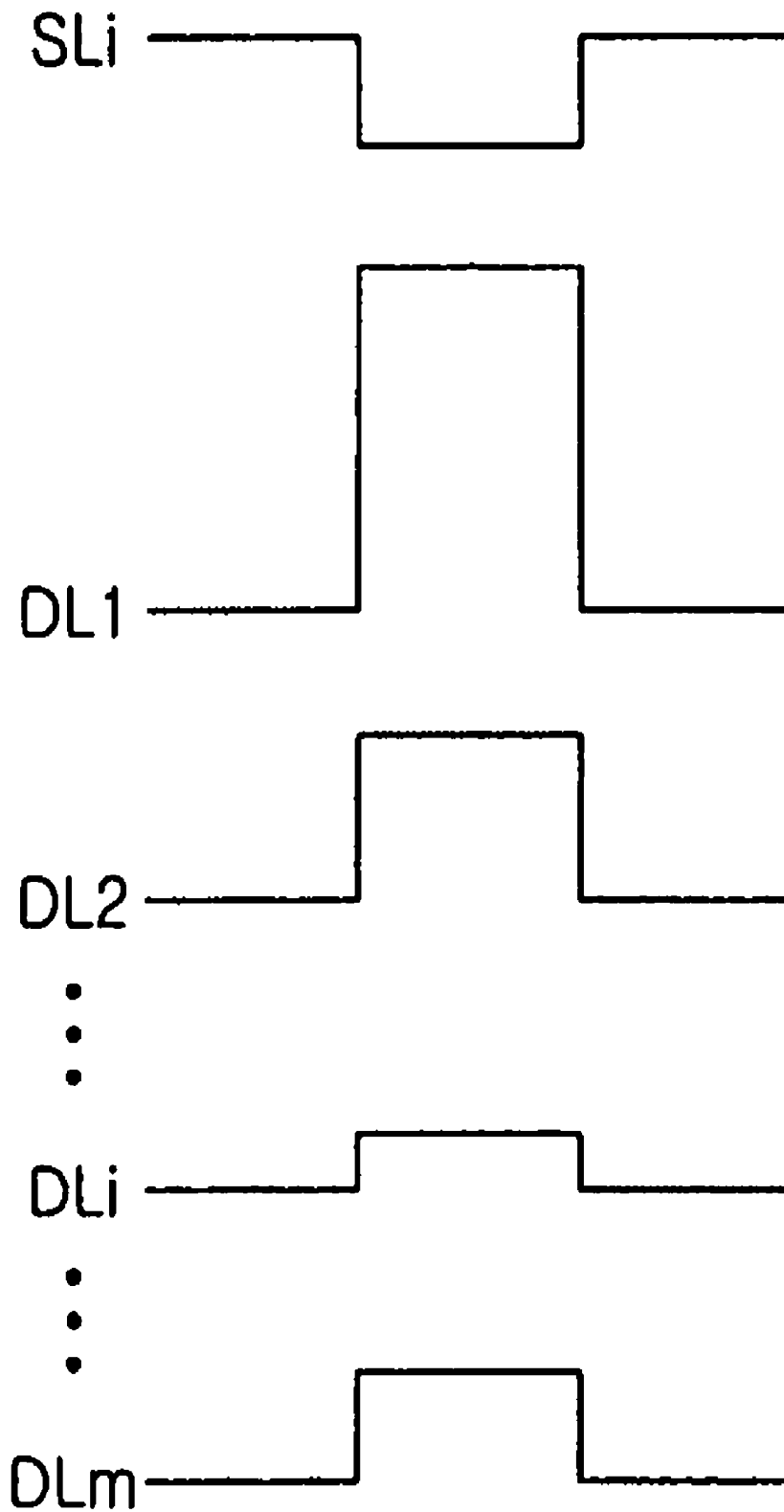
FIG. 3

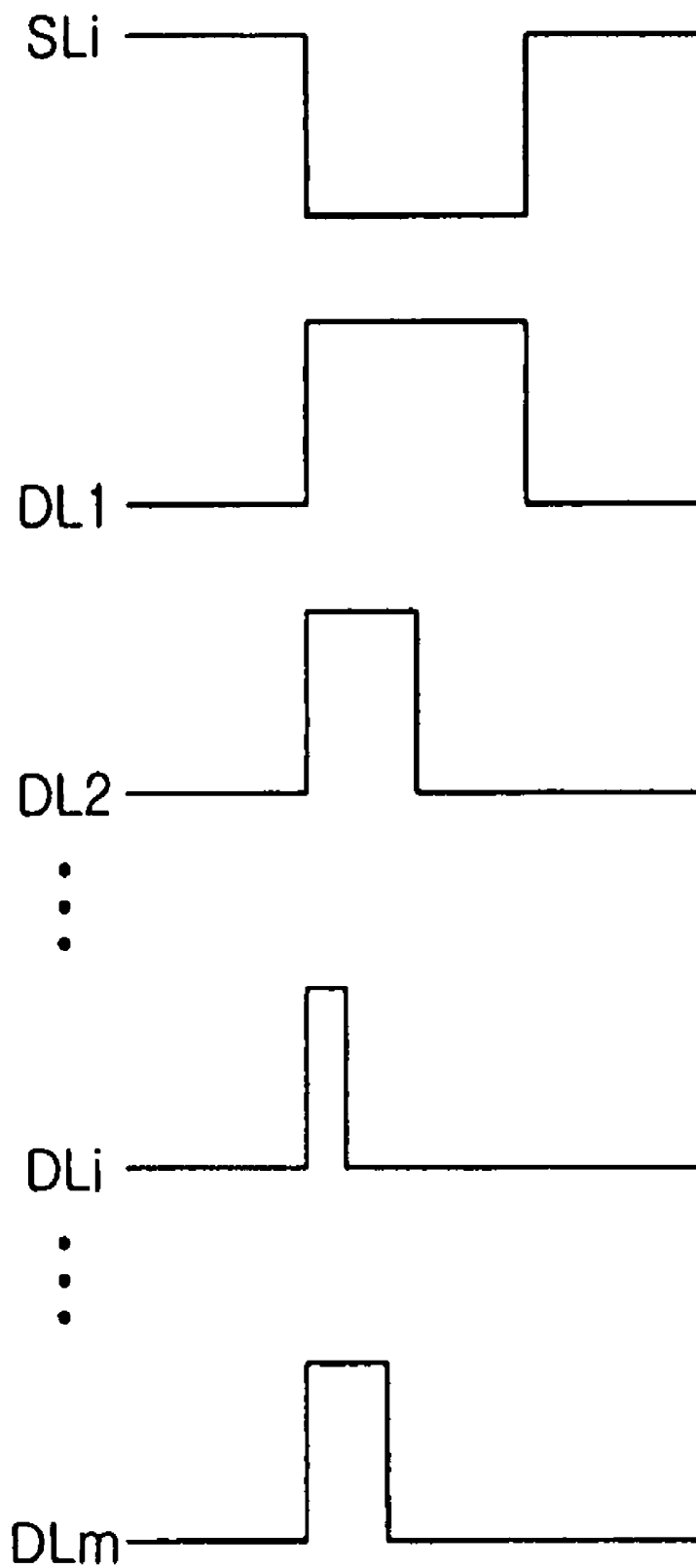
FIG. 4

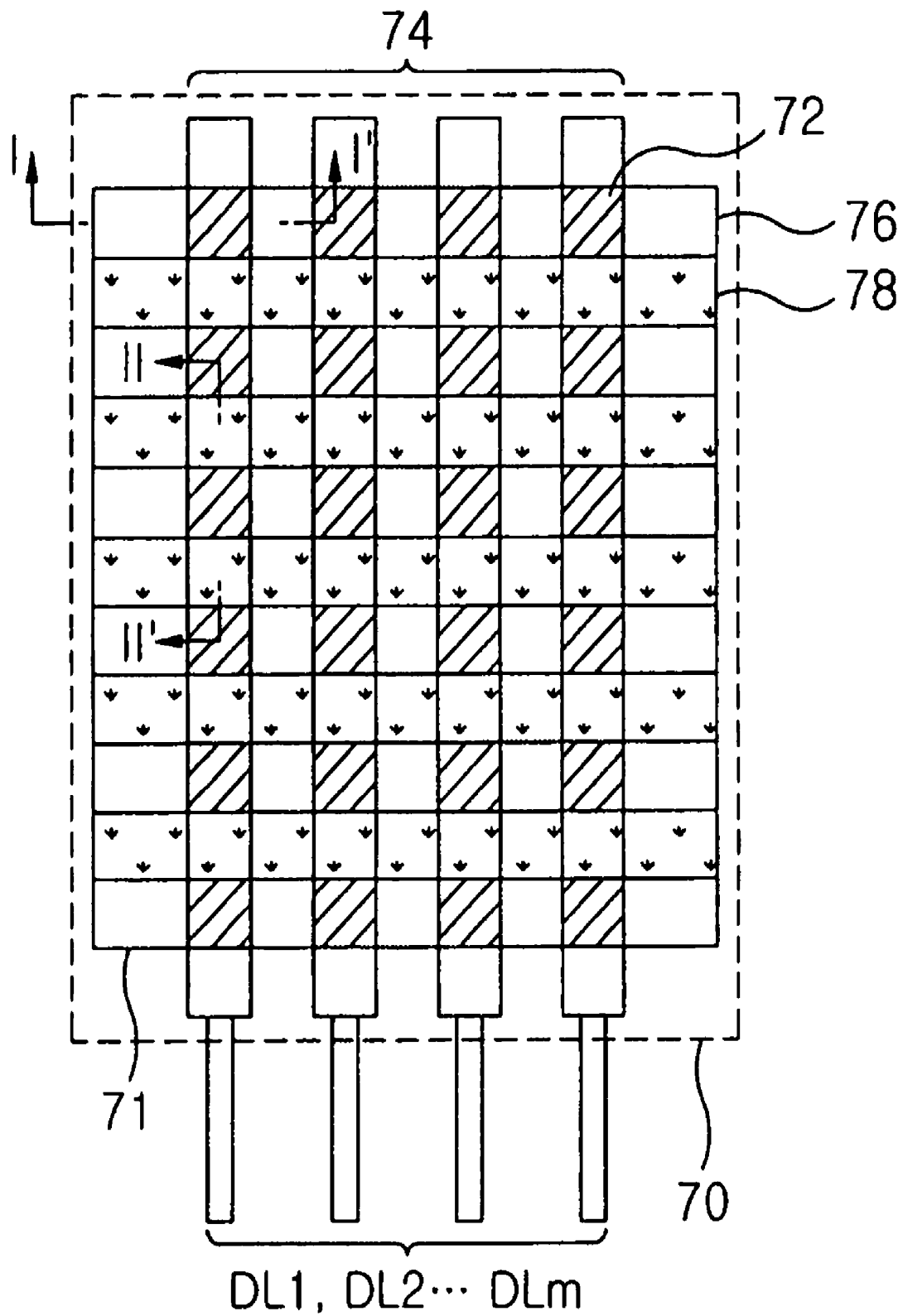
FIG. 5

FIG. 6

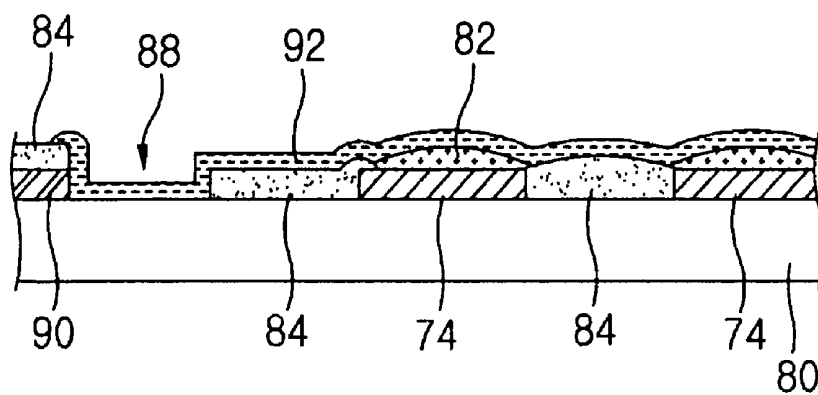


FIG. 7

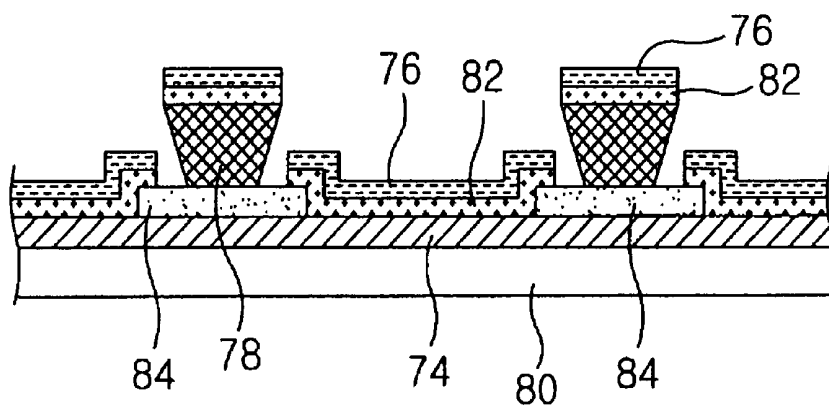


FIG. 8

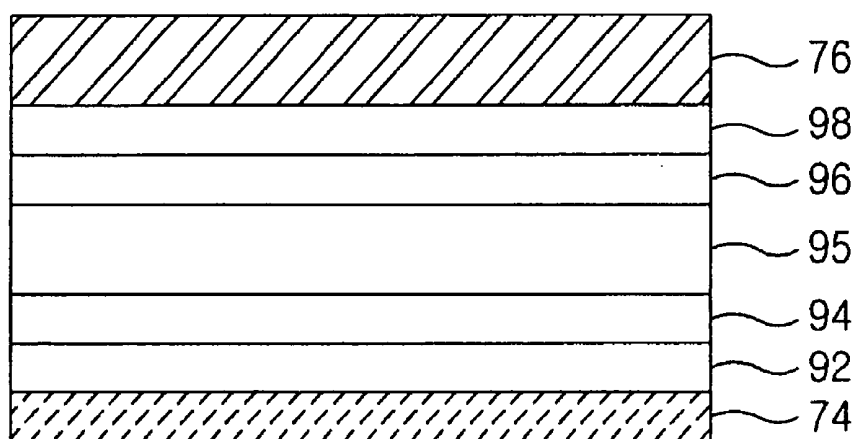


FIG. 9

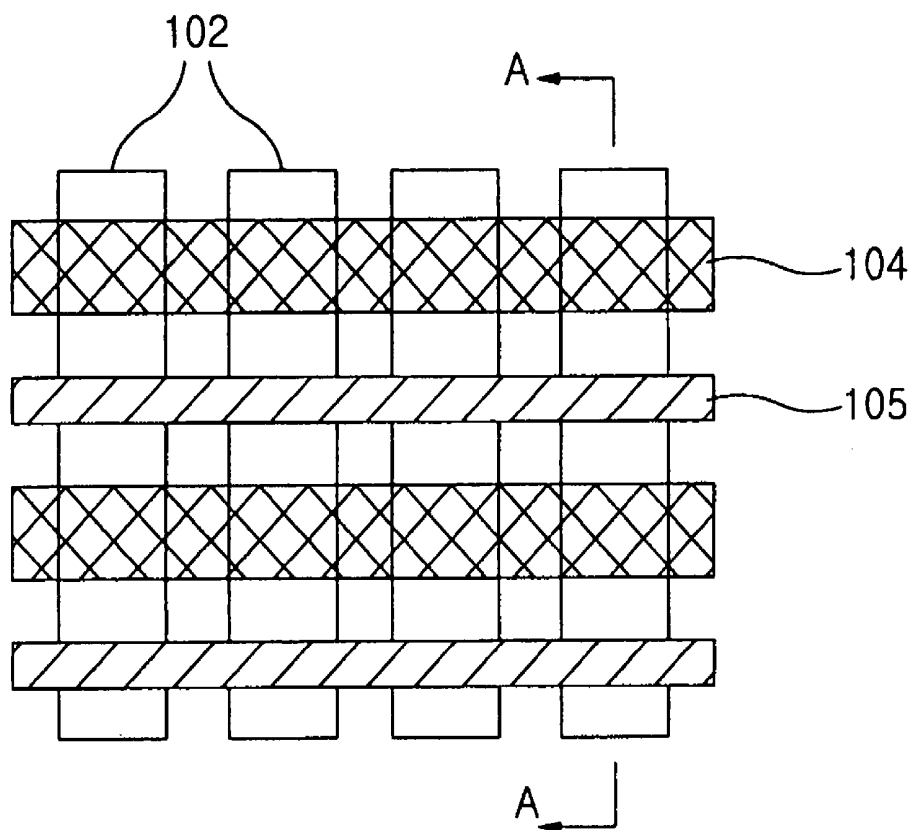


FIG. 10

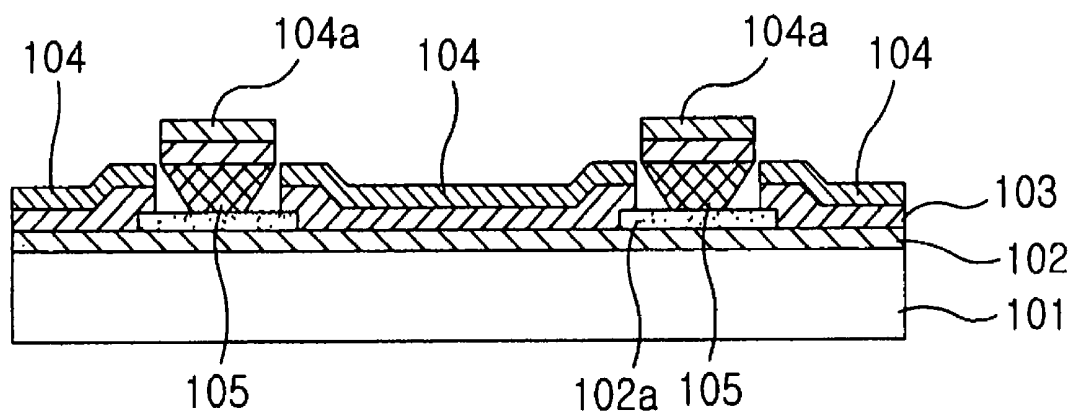


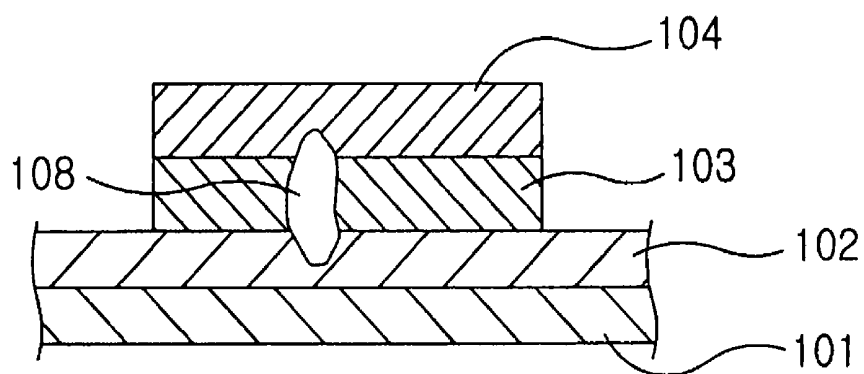
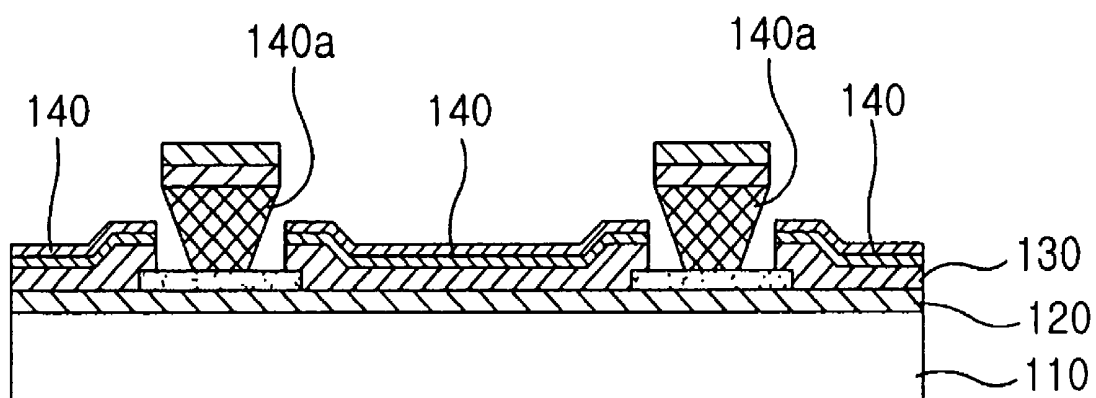
FIG. 11**FIG. 12**

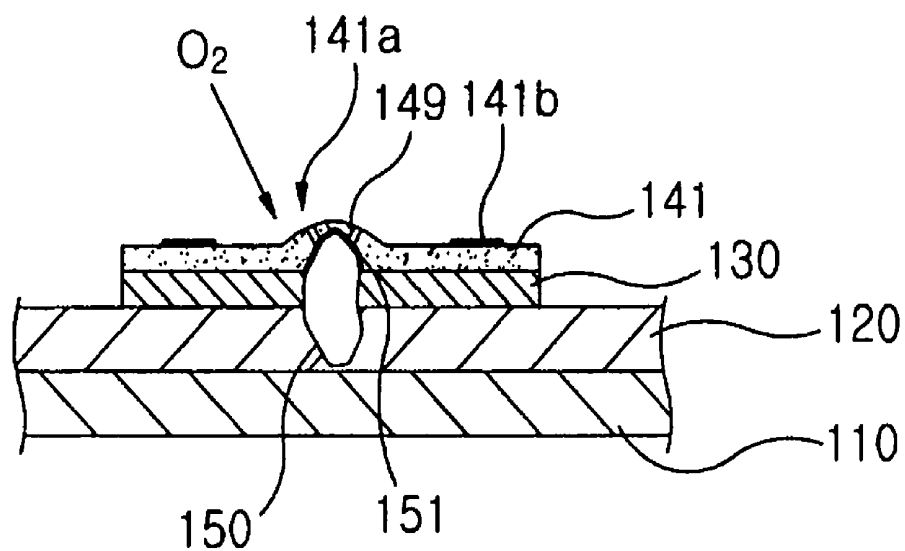
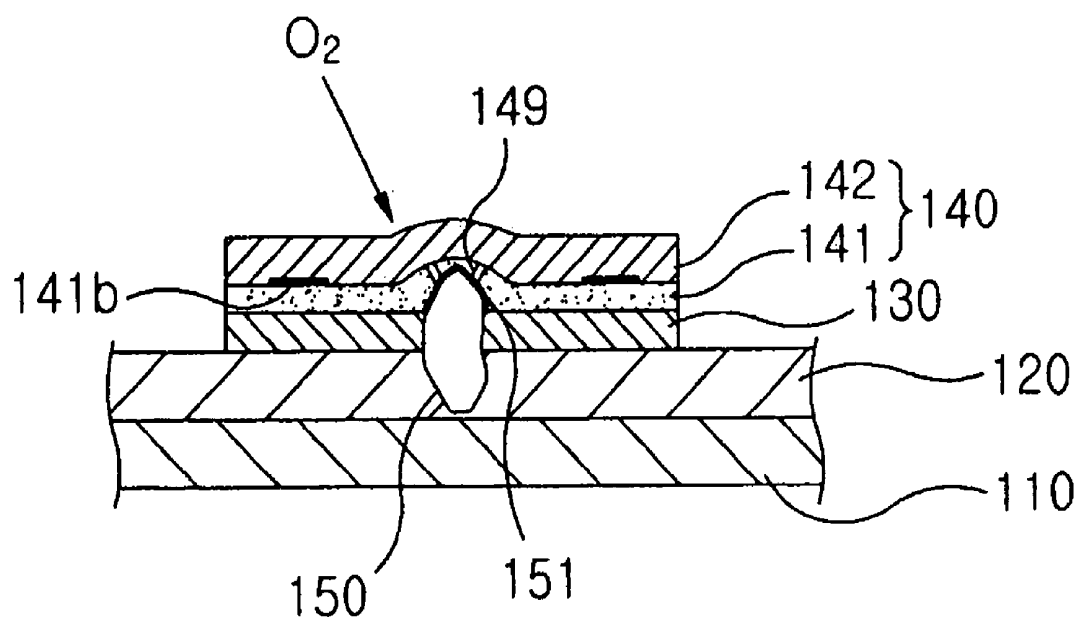
FIG. 13A**FIG. 13B**

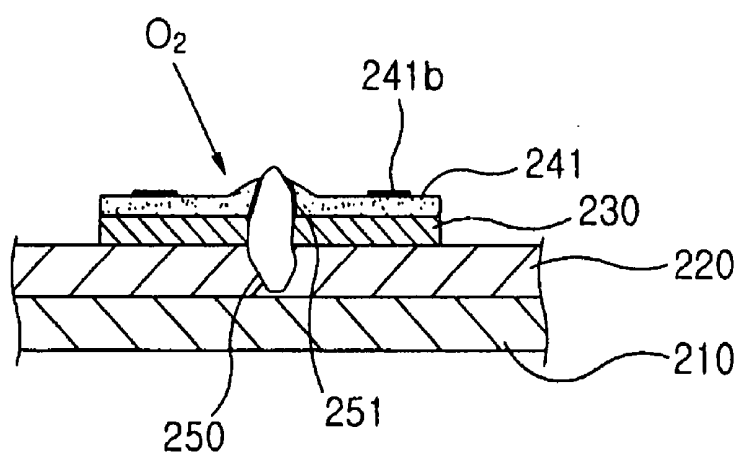
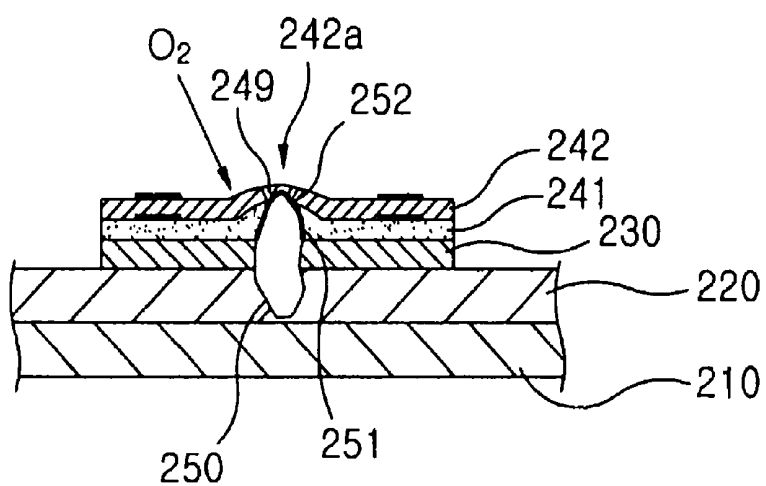
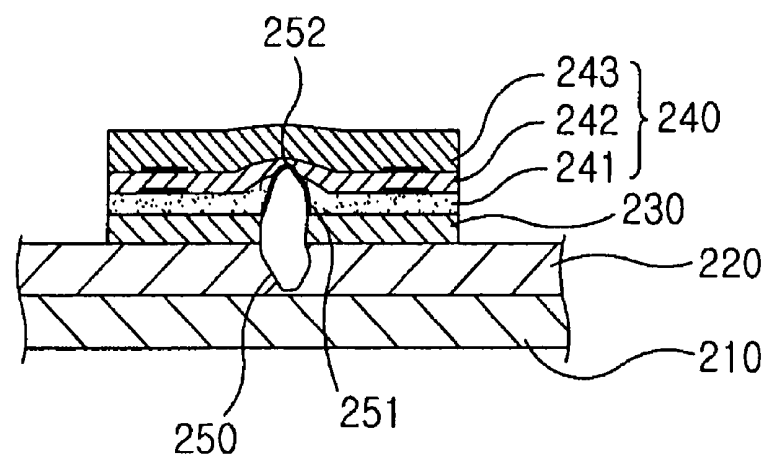
FIG. 14A**FIG. 14B****FIG. 14C**

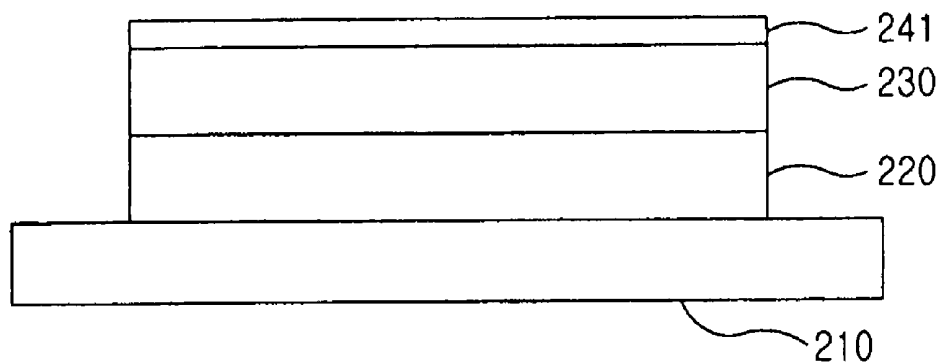
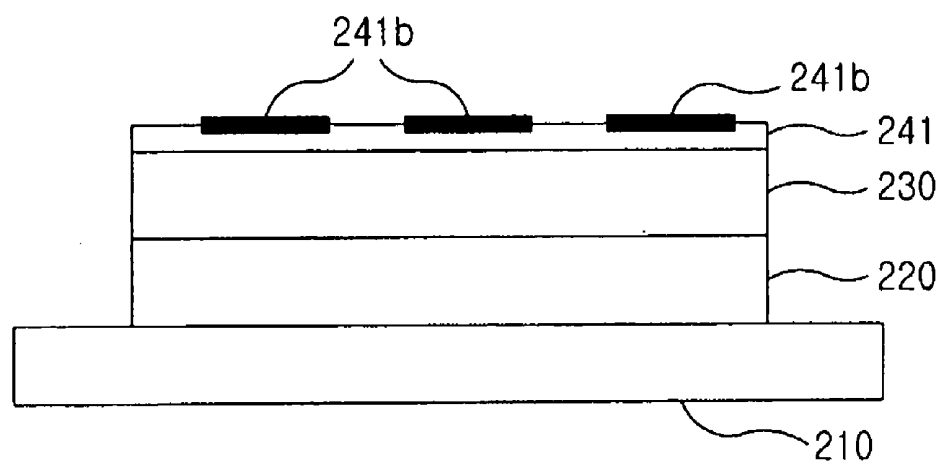
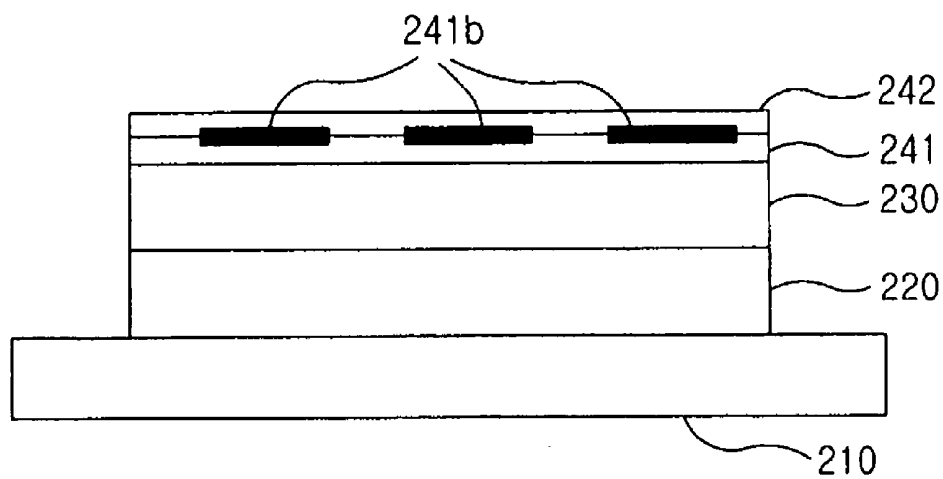
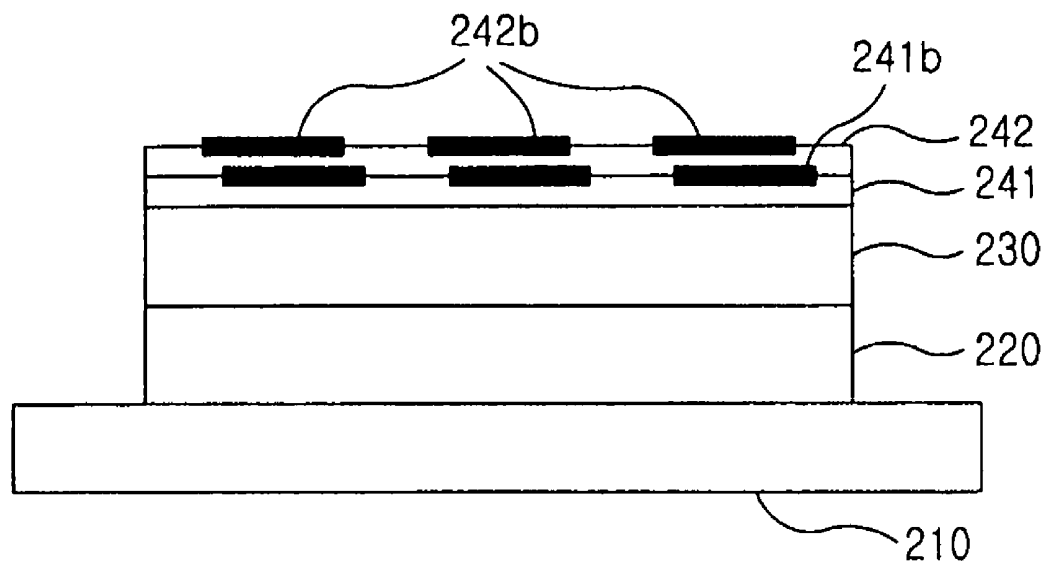
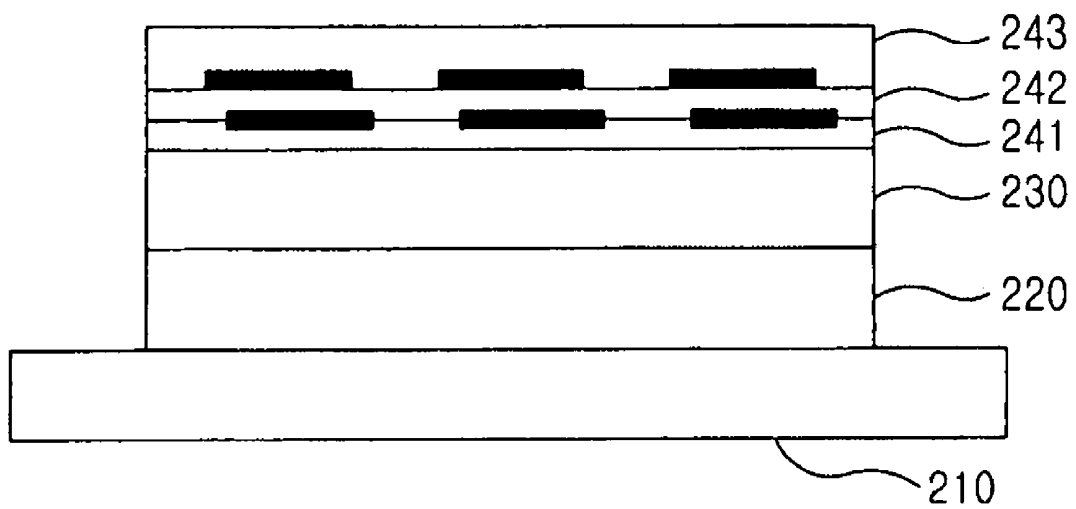
FIG. 15A**FIG. 15B****FIG. 15C**

FIG. 15D**FIG. 15E**

DISPLAY DEVICE AND METHOD FOR MANUFACTURING THE SAME

This application claims priority from Korean Patent Appli-
cation No. 10-2006-000099393, filed on Oct. 12, 2006, the
subject matter of which is incorporated herein by reference.

BACKGROUND

1. Field

Embodiments of the present invention may relate to a dis-
play device and/or a method for manufacturing a display
device. More specifically, embodiments of the present inven-
tion may relate to a display device and/or a method for manu-
facturing a display device that may prevent current leakage
from a cathode electrode and/or reduce resistance of the cath-
ode electrode.

2. Background

Various types of flat panel displays have been developed
with reduced weight and bulk that are free from disadvan-
tages of cathode ray tubes (CRT). Such flat panel displays
include a liquid crystal display (LCD), a field emission dis-
play (FED), a plasma display panel (PDP) and an electro-
luminescence (EL) display device.

BRIEF DESCRIPTION OF THE DRAWINGS

Arrangements and embodiments of the present invention
may be better understood with reference to the following
description, claims and accompanying drawings in which like
refer to like elements and wherein:

FIG. 1 is a block diagram of a display apparatus according
to an example arrangement;

FIG. 2 is a timing diagram showing one example of scan
signals being applied to scan lines according to an example
arrangement;

FIG. 3 is a timing diagram showing a method of driving a
panel using a pulse amplitude modulation (PAM) method;

FIG. 4 is a timing diagram showing a method of driving a
panel using a pulse width modulation (PWM) method;

FIG. 5 shows a panel according to an example arrange-
ment;

FIG. 6 is a side view of the panel according to an example
arrangement;

FIG. 7 is a side view of the panel according to an example
arrangement;

FIG. 8 shows an organic electroluminescent (EL) device
according to an example arrangement;

FIG. 9 is a plane view of a pixel circuit section of an organic
electroluminescent device according to one example arrange-
ment;

FIG. 10 is a sectional view taken along line A-A in FIG. 9;

FIG. 11 is a partial enlarged sectional view of one cathode
electrode and its understructure according to one example
arrangement;

FIG. 12 is a sectional view showing a structure of an
organic electroluminescent device according to an example
of the present invention;

FIG. 13A and FIG. 13B are partial enlarged views showing
(in sequence) a process of forming a cathode electrode
according to an example embodiment of the present inven-
tion;

FIGS. 14A-14C are partial enlarged views showing (in
sequence) a process of forming a cathode electrode in which
a particle is not completely covered with a first metal layer
according to an example embodiment of the present inven-
tion; and

FIGS. 15A-15E show a process of forming a cathode elec-
trode according to an example embodiment of the present
invention.

DETAILED DESCRIPTION

Embodiments of the present invention may be described in
detail with reference to the accompanying drawings. In the
following embodiments, an organic electroluminescent
device may be provided as one example of a light emitting
device. However, embodiments of the present invention are
not limited to an organic electroluminescent device.

FIG. 1 is a block diagram of a display apparatus according
to an example arrangement. Other arrangements may also be
provided such as, for example, in U.S. patent application Ser.
No. 10/858,387 (Publication No. 2004-222749), Ser. No.
11/858,387 (Publication No. 2004-222749), Ser. No. 11/318,
515 (Publication No. 2006-146827) and Ser. No. 11/289,644
(Publication No. 2006-119256), etc, whose entire disclosures
are incorporated herein by reference. A display apparatus
may be used in or formed as a rigid or flexible display for
electronic books, newspapers, magazines, etc. The display
apparatus may also be used in various types of portable
devices (e.g., handsets, MP3 players, notebook computers,
etc.), audio applications, navigation applications, televisions,
monitors, or other types of devices that use a display, either
monochrome or color.

FIG. 1 shows that the display apparatus may include a
panel 10, a data driving device 20, a scan driving device 30
and a control device 40. The panel 10 may also include a
plurality of pixels 50 formed in cross areas of data lines (DL1
to DLm) and scan lines (SL1 to SLn).

The scan driving device 30 may transmit scan signals in
sequence to the scan lines (SL1 to SLn). The data driving
device 20 may transmit data signals in sequence to the data
lines (DL1 to DLm). The data driving device 20 may use a
pulse amplitude modulation (PAM) method or a pulse width
modulation (PWM) method, for example, to apply the data
signals to the data lines (DL1 to DLm). For example, FIG. 2
is a timing diagram showing one example of scan signals
being applied to the scan lines by the scan driving device 30
and data signals being applied to the data lines by the data
driving device 20.

FIG. 3 is a timing diagram showing a method of driving the
panel 10 using a PAM method. The data driving device 20
may apply data signals (i.e., data current corresponding to the
digital video data) to the data lines (DL1 to DLm) by using the
PAM method. In the PAM method, a gray scale of the pixels
may be proportionate to an amplitude of the data current. In
the data current, a time to have high logic may be constant
irrespective of the gray scale corresponding to the digital
video data. Similar driving methods are disclosed in U.S.
patent application Ser. No. 11/318,515 (Publication No.
2006-146827), etc, whose entire disclosure is incorporated
herein by reference.

FIG. 4 is a timing diagram showing a method of driving the
panel 10 using a PWM method. The data driving device 20
may apply data signals (i.e., data current corresponding to the
digital video data) to the data lines (DL1 to DLm) by using the
PWM method. In the PWM method, a gray scale of the pixels
may be proportionate to a time of high logic in the data
current. The amplitude of the data current may be constant
irrespective of the gray scale corresponding to the digital
video data. Similar driving methods are disclosed in U.S.
patent application Ser. No. 11/318,515 (Publication No.
2006-146827), etc., whose entire disclosures is incorporated
herein by reference.

The data driving device **20** use either a PAM current generating circuit and/or a PWM current generating circuit to drive the panel **10** depending on a gray scale level of an image signal as detected by the control device **40**. When image signals having a relatively high gray scale level are to be displayed, the PAM method may be used to minimize power consumption. When image signals having a relatively low gray scale level are to be displayed, the PWM method may be used to ensure that good image quality is maintained. Other methods may also be used.

FIG. **5** shows a structure of a panel **10** according to an example arrangement. Other arrangements may also be used such as, for example, as illustrated in U.S. Pat. No. 6,897,471, etc., whose entire disclosure is incorporated herein by reference. More specifically, FIG. **5** shows a panel **70** corresponding to the panel **10** shown in FIG. **1**. The panel **70** may include a cell section **71** containing a plurality of sub-pixels **72** (e.g., light emitting areas), anode electrode layers (or anode electrodes or data electrodes) **74**, cathode electrode layers (or cathode electrodes or scan electrodes) **76** and walls **78**. The sub-pixels **72** may be formed in cross areas of the anode electrode layers **74** and the cathode electrode layers **76**.

The anode electrode layers **74** may serve as positive electrodes and the cathode electrode layers **76** may serve as negative electrodes. The walls **78** may be made of an insulating material to separate the cathode electrode layers **76** so that the cathode electrode layers **76** are not short-circuited.

The data lines DL1, DL2 . . . DLm may be conductors that are coupled to the anode electrode layers **74**. Scan lines (not shown in FIG. **5**) may be coupled to the cathode electrode layers **76**. As one example, first scan lines may be connected to odd number cathode electrode layers and second scan lines may be connected to even number cathode electrode layers.

FIGS. **6** and **7** are side views of an electroluminescent panel according to an example arrangement. More specifically, FIG. **6** is a sectional view taken along line I-I' of FIG. **5** and FIG. **7** is a sectional view taken along line II-II' of FIG. **5**. Other arrangements may also be used.

FIG. **6** shows a substrate **80** having the anode electrode layers **74** and light emitting layer (or layers) **82** formed thereon in sequence. Each of the light emitting layers **82** may include an emitting layer made of organic or inorganic material corresponding to red, green or blue light, or a combination thereof.

An insulating layer **84** (or layers) may be formed on areas of the substrate **80** other than the light emitting areas and a contact hole section **88**. The insulating layer **84** may prevent a short from occurring between the anode electrode layers **74**. A scan line **90** may be connected to the contact hole section **88**.

A metal layer **92** may be formed on the substrate **80** over the anode electrode layers **74**, the insulating layer **84**, the light emitting layer **82** and the scan line **90**. The metal layer **92** may be connected to the scan line **90** through the contact hole section **88**. The cathode electrode layers **76** (not shown in FIG. **6**) may be connected to the scan line **90** through the contact hole section **88**.

FIG. **7** shows that the anode electrode layer **74**, the light emitting layer **82** and the cathode electrode layer **76** may be formed in sequence on the substrate **80**. In addition, the insulating layers **84** and the wall **78** may be formed in sequence on the anode electrode layer **74**.

FIG. **8** shows details of the light emitting device (e.g., an organic electroluminescent device) according to an example arrangement. Other arrangements may also be used such as, for example, as illustrated in U.S. Pat. Nos. 6,579,629, 6,614, 176, & 6,803,123, and U.S. patent application Ser. No.

11/102,358 (Publication No. 226767), etc., whose entire disclosures are incorporated herein by reference. The plurality of layers shown in FIG. **8** correspond to the light emitting layer **82** shown in FIGS. **6-7**. More specifically, the device includes a hole injecting layer (HIL) **92** formed on the anode electrode **74**, a hole transporting layer (HTL) **94** formed on the HIL **92**, an organic electroluminescent layer **95** formed on the HTL **94**, an electron transporting layer (ETL) **96** formed on the HTL **94** and an electron injecting layer (EIL) **98** formed on the ETL **96**. The cathode electrode layer **76** may be formed on the ETL **96**. One or more of the HIL, HTL, ETL and EIL may be omitted, depending on the particular device structure adopted. Further, an inorganic electroluminescent device may be used.

Still further, depending on the materials used for the cathode electrode, the anode electrode and/or the substrate, the electroluminescent device may emit light through a transparent cathode electrode, or through a transparent anode electrode and the substrate, or through both (i.e., bi-directional).

Arrangements and embodiments will now be described in more detail with respect to FIGS. **9-14**.

FIG. **9** is a plane view of a pixel circuit section of an organic electroluminescent device according to one example arrangement. FIG. **10** is a sectional view taken along a line A-A in FIG. **9**. FIGS. **9-10** schematically show a structure of the organic electroluminescent device. Other arrangements may also be used.

The organic electroluminescent device may include anode electrodes **102** arranged on a substrate **101**, an organic electroluminescent light emitting layer **103** formed on the anode electrode **102** and cathode electrodes **104** formed on the organic electroluminescent light emitting layer **103**. The anode electrodes **102** may be an ITO layer (or a flexible transparent layer). The cathode electrodes **104** may be a metal layer mainly formed of aluminum.

Each of the cathode electrodes **104** (including the organic electroluminescent light emitting layer **103**) may be spaced apart from a neighboring cathode electrode(s) by a wall **105**. FIG. **10** also shows an insulating layer **102a** and a metal layer **104a** formed on the wall **105** in a process of forming the cathode electrode **104**.

After a plurality of pixel circuit sections having the structure shown in FIGS. **9-10** are formed on the substrate **101**, individual organic electroluminescent devices may be formed by a metal wiring process (to the anode electrodes **102** and the cathode electrodes **104**), a cap attaching process and a scribing process in each pixel circuit section.

FIG. **11** is a partial enlarged sectional view of one cathode electrode **104** and its understructure according to one example arrangement. Other arrangements may also be used. The understructure may include the substrate **101** and the anode electrode **102**. The cathode electrode **104** provided on the organic electroluminescent light emitting layer **103** may be made of metal, such as aluminum. The cathode electrode **104** may be referred to as a "metal electrode."

In the process of forming the organic electroluminescent light emitting layer **103**, a conductive particle (or particles) **108** may be generated due to one factor. For example, the conductive particle **108** may be generated due to impurity particles existing in a process chamber. The particles **108** may exist in the organic electroluminescent light emitting layer **103**. Additionally, the particles **108** may exist in the metal electrode **104** formed on the organic electroluminescent light emitting layer **103** after forming the metal layer.

As shown in FIG. **11**, the conductive particle (or particles) **108** existing over the anode electrode **102**, the organic electroluminescent light emitting layer **103** and the metal elec-

trode **104** may be responsible for leakage current. Although no current should flow, a reverse voltage may be applied. However, if the conductive particle **108** exists then a current may flow through the metal electrode **104**, the organic electroluminescent light emitting layer **103** and the anode electrode **102** due to the conductive particle **108**.

FIG. **12** is a sectional view showing a structure of an organic electroluminescent device according to an example embodiment of the present invention. FIG. **13A** and FIG. **13B** are partial enlarged views showing (in sequence) a process of forming a cathode electrode according to an example embodiment of the present invention. Other embodiments and configurations are also within the scope of the present invention. The cathode electrode **140** may hereinafter be referred to as "a metal electrode."

As shown in FIG. **13A**, an anode electrode **120** and an organic electroluminescent light emitting layer **130** may be formed on a substrate **110**. In a process of forming the organic electroluminescent light emitting layer **130**, a conductive particle **150** may be generated such as due to impurity particles existing in a process chamber. The conductive particle **150** may also be provided due to other factors. The conductive particle **150** may exist in the organic electroluminescent light emitting layer **130**. The organic electroluminescent light emitting layer may hereinafter be referred to as an organic EL layer **130**.

In the process of manufacturing the organic electroluminescent device, it may be difficult to identify whether the conductive particle **150** exists in the structure. It may also be difficult to prevent generation of the conductive particle **150** during manufacturing.

An example embodiment of the present invention may solve a problem or problems that occur when a conductive particle exists in the structure (regardless of an actual existence of the conductive particle).

FIG. **13A** shows a first metal layer **141** (i.e., a lower metal layer or a first conductive layer) formed on the organic EL layer **130** through a process of forming the metal layer in a vacuum chamber.

The first metal layer **141** may be formed through a thermal chemical vapor deposition process or an E-beam deposition process when covering the organic EL layer **130** and the conductive particle **150** existing on the organic EL layer **130**. Other processes of forming the first metal layer **141** may also be used.

The substrate **110** may then be introduced into a chamber to perform a first oxidation process. The chamber in which the first oxidation process is performed may contain an inert gas in a range of 85% to 98% by volume and oxygen (O_2) in a range of 2% to 15% by volume. The inert gas may be argon, nitrogen or a mixture thereof, for example.

Once the oxidation process is performed (e.g., for 20 minutes) and/or during the oxidation process, oxygen may react with metal material constituting the first metal layer **141** formed around the conductive particle **150**. An oxide layer **151** (or other types of insulating layer) may be formed on a portion **141a** of the first metal layer **141** corresponding to the conductive particle **150**. The oxide layer **151** may be adjacent to the first metal layer **141**.

The oxidation reaction will now be described. In the first metal layer **141** formed on the organic EL layer **130**, since a portion formed on a region on which the conductive particle **150** does not exist is dense and the surface is flat (or substantially flat), that portion of the first metal layer **141** may not react with oxygen.

If a process time is lengthened and a ratio of oxygen (i.e., the range of 2% to 15% by volume) in an entire reaction gas

contained in the chamber is high, the first metal layer **141** may react with oxygen to form the oxide layer on the surface. However, in an example embodiment of the present invention, conditions may be controlled to a range of 2% to 15% by volume of O_2 and approximately twenty (20) minutes of process time so as to not form the oxide layer on the first metal layer **141**.

On the other hand, the surface of the conductive particle **150** may not be uniform, and so the portion **141a** of the first metal layer **141** formed on the conductive particle **150** may have an irregular fabric and shape. More specifically, micro cracks **149** may occur on the portion **141a** of the first metal layer formed on the conductive particle **150** having the irregular shape or on a region adjacent to the conductive particle **150** due to the irregular shape of the conductive particle **150**.

Oxygen may penetrate to the conductive particle **150** through the micro cracks **149** formed on the portion **141a** of the first metal layer **141** corresponding to the conductive particle **150**. The penetrated oxygen may move along an interface (i.e., a micro space) between the irregular surface of the conductive particle **150** and the first metal layer **141**. The oxygen may react with the metal material constituting the first metal layer **141** corresponding to the conductive particle **150**.

Due to the reaction between the metal material constituting the first metal layer **141** and oxygen, the oxide layer **151** may form on the surface of the first metal layer **141** that contacts the conductive particle **150**. The oxide layer **151** may exist on the interface between the conductive particle **150** and the first metal layer **141**. A width (i.e., a dimension) of the oxide layer **151** may be smaller than a width of the first metal layer **141**.

If the oxidation process is carried out in the chamber under a condition that a ratio of oxygen is more than 15% in volume, for twenty minutes or more, the oxygen may react with the metal material constituting the first metal layer **141**. The oxide layer **151** may be formed on a region of the first metal layer **141** on which the particle **150** does not exist. Under the above condition, oxygen may penetrate to the organic EL layer **130** through various paths and the organic EL layer **130** may be oxidized.

Since the first metal layer **141** functions as a cathode electrode together with other metal layers formed in a stack on the first metal layer **141**, the oxide layer **151** may have a significant influence on the function of the electrode if the oxide layer **151** is formed on the first metal layer **141**.

On the other hand, if the oxidation process is carried out in a chamber such that a ratio of oxygen is less than 2% in volume for less than twenty minutes, the oxide layer **151** may not form on a flat surface (or shape) of first metal layer **141** or a thin oxide layer may be formed that does not influence the conductive function of the first metal layer **141**. However, the oxide layer **151** with a sufficient thickness may not form on the interface between the conductive particle **150** and the first metal layer **141**, and the oxide layer **151** may not prevent current from being leaked. Also, under the above condition, the oxidation process may be carried out for a long time (e.g., more than twenty minutes) to obtain the oxide layer with a sufficient thickness.

The first metal layer **141** may satisfy conditions in order to obtain an optimum effect in a process of forming the oxide layer **151** on an interface between the conductive particle **150** and the first metal layer **141**.

The material for forming the first metal layer **141** may be one (or more) from a group consisting of aluminum, manganese, magnesium, calcium, and an alloy thereof that can react with oxygen as a reaction gas in the oxidation process. Accordingly, the oxide layer **151** formed on the interface between the conductive particle **150** and the first metal layer

141 may be aluminum oxide (Al_2O_3), manganese oxides (MnO_x), magnesium oxides (MgO_x) or calcium oxides (CaO_x). Other oxide layers are also within the scope of the present invention.

The first metal layer **141** may have a thickness in a range of from 1 nm to 100 nm. As another example, the first metal layer **141** may have a thickness in a range of from 60 nm to 70 nm. Other thicknesses and ranges are also within the scope of this disclosure.

If the thickness of the first metal layer **141** is less than 1 nm, oxygen may pass through the first metal layer **141** in the oxidation process and penetrate the organic EL layer **130**. The organic EL layer **130** may be damaged by the oxygen.

On the other hand, if the thickness of the first metal layer **141** is more than 100 nm, oxygen may not pass through the first metal layer **141** or reach the conductive particle **150**. Consequently, the oxide layer **151** may not be formed on the surface of the metal layer **141** contacting the conductive particle **150**.

The oxidation process condition described above (i.e., the ratio of oxygen in the range of 2% to 15% by volume and the process time of twenty minute) is merely one example. Embodiments of the present invention are not limited thereto. For example, if the ratio of oxygen in the chamber in which the oxidation process is performed is more than 15% by volume, then the oxidation process time may be less than twenty minutes. On the other hand, if the ratio of oxygen in the chamber is less than 2% by volume, then the process time may be more than twenty minutes. Embodiments of the present invention may include other ratios and times.

Thus, the oxidation process conditions may be selected in various ranges considering factors such as the metal layer material on which the oxidation reaction occurs, a volume ratio of oxygen in the chamber in which the oxidation process is carried out, a process time, and/or a formation rate (i.e., thickness) of the oxide layer.

After performing the oxidation process, a second metal layer **142** (i.e., an upper metal layer or second conductive layer) constituting a lower metal layer may be formed on the first metal layer **141** as shown in FIG. 13B.

If the size of the conductive particle **150** is relatively small and the first metal layer **141** completely covers (or substantially covers) the entire surface of the conductive particle **150**, the oxidation process may not be performed after forming the second metal layer **142** on the first metal layer **141**.

The thickness of the oxide layer **151** formed around portions of the conductive particle **150** may be calculated or determined utilizing process conditions of the first oxidation process. The process conditions may include a volume ratio of oxygen, a process time, a reactivity of a material constituting the first metal layer **141** with oxygen, etc.

The thickness of the oxide layer **151** may be calculated by measuring leakage current to another device that occurs through the first oxidation process of a same condition or similar conditions. When compared with a device that does not include the oxidation process, if the leakage current of the device that includes the oxidation process is remarkably lower, the leakage current in the device caused by the conductive particle **150** may be significantly reduced through the first oxidation process.

If a leakage current caused by the conductive particle **150** is remarkably reduced by the oxide layer **151** formed on an interface between the conductive particle **150** and the first metal layer **141** by the first oxidation process, then the process for forming a third metal layer may be carried out without performing a second oxidation process.

Accordingly, due to the oxide layer **151** existing on the interface between the first metal layer **141** and the conductive particle **150**, the conductive particle **150** may be electrically insulated from the first metal layer **141** and leakage current caused by the conductive particle **150** may not occur (or may be reduced). Also, the metal electrode **140** (including the plurality of metal layers **141** and **142**) may have a relatively large thickness. Accordingly, a resistance of the metal electrode **140** may become smaller.

Here, as described above, a thickness of the first metal layer **141** to which oxygen penetrates in the oxidation process should be restricted (about 1 to 100 nm). However, in order to minimize a resistance and maintain a function of the metal electrode as the electrode, the metal electrode **140** must have a certain thickness. As shown in FIG. 13B, accordingly, compared with a restricted thickness of the first metal layer **141**, the second metal layer **142** has a thickness which is the same as or thicker than that of the first metal layer **141** so that the metal electrode **140** consisting of the first metal layer **141** and the second metal layer **142** can perform naturally the function of the electrode and has a low resistance.

On the other hand, the first and second metal layers **141** and **142** constituting the metal electrode **140** may be formed of a same or similar metal material (e.g. aluminum, magnesium, calcium or alloy thereof). The first and second metal layers **141** and **142** may also be formed of different metal materials.

If the first and second metal layers **141** and **142** each are formed of different metal materials, an order for forming (i.e., stacking) the first and second metal layers **141** and **142** may be decided based on a work function of each metal material.

The work function may be a term representing energy required for discharging an electron at an absolute zero point in terms of an electron-volt (eV) unit. Energy such as heat or light may be applied to an electron in order to discharge the electron in the metal (or semiconductor) from a surface to an exterior.

The work function may depend on a kind of metal. For example, the work functions of sodium, barium, gold, platinum and tungsten may be 2.28 eV, 2.51 eV, 4.09 eV, 5.32 eV and 4.52 eV, respectively. Accordingly, the arrangement of the first and second layers **141** and **142** discharging electrons may be decided after considering the work function of a metal material forming the metal layers.

As described above, on the other hand, in the oxidation process carried out after forming the first metal layer **141**, the oxide layer **141b** can be formed partially on a surface of the first metal layer **141**. The oxide layer **141b** formed on a surface of the first metal layer **141** can function as an insulating layer preventing an electric flow between the first metal layer **141** and the second metal layer **142** forming one metal electrode.

Accordingly, it is preferred that the oxide layer **141** is not formed on the first metal layer **141** or the oxide layer **141b** has a minimum surface area. For example, the oxide layers **141b** are formed such that a distance between the adjacent oxide layers **141b** is 1 nm or more, and so an electric flow between the first metal layer **141** and the second layer **142** is not prevented and the metal electrode **140** can perform normally its function.

Here, by controlling the conditions (a volume ratio of oxygen and a process time) of the oxidation process, a distance between the adjacent oxide layers **141b** corresponding with the above conditions can be obtained.

On the other hand, the method of manufacturing the display device (that is, the method of forming the metal electrode) according to the present invention may further com-

prise the step of applying an inverse bias voltage after a process of forming the oxide layer.

A great quantity of oxygen used for forming the oxide layer is existed in the chamber after the process of forming the oxide layer. Under this condition, if the inverse bias voltage is applied to the device, the micro crack **149** of the first metal layer **141** corresponding to the conductive particle **150** is expanded, and so oxygen existed in the chamber is introduced additionally into a space between the conductive particle **150** and the first metal layer **141** through the expanded micro crack **149**. Consequently, in addition to the oxide layer **151** which is already formed on the first metal layer **141**, the oxide layer with a sufficient thickness is additionally formed.

In the above description, although the step for applying the inverse bias voltage is performed after forming the oxide layer on the first metal layer **141**, the inverse bias voltage can be applied in process of forming the oxide layer to obtain the same effect.

FIGS. **14A-14C** are partial enlarged views showing (in sequence) a process of forming a metal electrode (i.e., a cathode electrode) in which a conductive particle is not covered completely by a first metal layer according to an example embodiment of the present invention. Other configurations and embodiments are also within the scope of the present invention.

If a size of the conductive particle **250** is relatively large, a first metal layer **241** (or first conductive layer) may be formed having a thickness as in the above described range (i.e., from 1 nm to 100 nm). However, the conductive particle **250** may not be completely covered by the first metal layer **241** and a portion thereof may be exposed outside of the first metal layer **241**.

An oxide layer **251** (or insulating layer) formed by the first oxidation process (as described above with reference to FIG. **13A**) may exist on the interface between the first metal layer **241** and the conductive particle **250**. However, the oxide layer **251** may not exist on a surface of the conductive particle **250** exposed outside of the first metal layer **241**. A width (i.e., a dimension) of the oxide layer **251** may be smaller than a width of the first metal layer **241**.

A second metal layer **242** (or second conductive layer) formed on the first metal layer **241** may contact the exposed portion of the conductive particle **250** as shown in FIG. **14B**. Leakage currents in the device that passes through the first oxidation process and leakage current in another device that does not pass through the oxidation process may not have much of a difference.

Although the first oxidation process may be carried out when the second metal layer **242** formed on the first metal layer **241** contacts the exposed portion of the conductive particle **250**, leakage may also occur through the conductive particle **250**. Accordingly, a second oxidation process may be performed.

After the first oxidation process, the second metal layer **242** constituting the lower metal layer may be formed on the first metal layer **241** through the metal layer forming process as shown in FIG. **14B**.

Since the size of the conductive particle **250** may be large, a crack **249** may be formed on a portion **242a** of the second metal layer **242** corresponding to the conductive particle **250**.

After the process for forming the second metal layer **242**, the second oxidation process may be carried out in a chamber having an oxygen atmosphere. The oxygen may penetrate through the crack **249** existing on a portion **242a** of the second metal layer **242** corresponding to the conductive particle **250**.

Oxygen may reach the conductive particle **250** and then react with metal material constituting the second metal layer

242 adjacent to the conductive particle **250** so as to form an oxide layer **252** (or insulating layer) on a surface of the second metal layer **242**. The oxide layer **252** may exist on an interface between the second metal layer **242** and the conductive particle **250**. A width of the oxide layer **252** may be smaller than a width of the second metal layer **242**.

A third metal layer **243** (i.e., an upper metal layer) or third conductive layer may be formed on the second metal layer **242** through a metal layer forming process as shown in FIG. **13B**. Accordingly, a multi-layered metal electrode **240** may be formed on the organic EL layer **230**. The multi-layered metal electrode **240** may include the first and second metal layers **241** and **242** (as the lower metal layer) and the third metal layer **243** (as the upper metal layer).

A third oxidation process may be carried out in an oxygen chamber under a same condition as the first and second oxidation processes. On the other hand, if the current leakage is remarkably reduced or is not generated at all in the device through the first and second oxidation processes, the third oxidation process may not be carried out.

In the multi-layered metal electrode **240** (as shown in FIG. **14C**) formed through the above processes, the conductive particle **250** may exist. However, oxygen may penetrate the first and second metal layers **241** and **242** and react with metal material constituting the first and second metal layers **241** and **242** corresponding to the conductive particle **250** in the first and second oxidation processes.

Accordingly, due to the oxide layer **251** existing on an interface between the first metal layer **241** and the conductive particle **250** and the oxide layer **252** existing on an interface between the second metal layer **242** and the conductive particle **250**, the conductive particle **250** may be completely and electrically insulated from the first and second metal layers **241** and **242**. Accordingly, leakage current caused by the conductive particle **250** may not occur and/or may be substantially reduced.

In at least one embodiment the oxidation process may be exemplified by the first oxidation process after forming the first metal layer **241** as the lower metal layer and the second oxidation process after forming the second metal layer **242**. However, one oxidation process may be carried out after forming the lower metal layer including the first and second metal layers **241** and **242**.

The metal layer forming process may be performed repeatedly (i.e., at least twice) to form the cathode (metal) electrode having a multi-layered structure, thereby making the cathode become thicker. As a result, embodiments of the present invention may reduce resistance of the cathode electrode.

In addition, since the oxidation process is carried out after forming the metal layer, the oxide layer may be formed around the conductive particle (i.e., on the interface between the conductive particle and the metal layer) and so leakage current by the conductive particle may be prevented and/or reduced.

Here, as described above, a thickness of the lower metal layer (that is, the first metal layer **241** and the second metal layer **242**) to which oxygen penetrates in the oxidation process should be restricted. However, in order to minimize a resistance and maintain a function of the metal electrode as the electrode, the metal electrode **240** must have a certain thickness. As shown in FIG. **14C**, accordingly, compared with a restricted thickness of the lower metal layer (the first metal layer **241** and the second metal layer **242**), the third metal layer **243** (the upper metal layer) has a thickness which is the same as or thicker than that of the lower metal layer so that the metal electrode **240** consisting of the first, second and third

metal layers **241**, **242** and **243** can perform naturally the function of the electrode and has a low resistance.

On the other hand, the condition regarding a distance between the adjacent oxide layers formed on each of the first metal layer **241** and the second metal oxide layer **242** and the step for applying the inverse bias voltage after forming the oxide layer or in process of forming the oxide layer are the same as the condition regarding a distance between the adjacent oxide layers and the step for applying the inverse bias voltage in the above description described previously with reference to FIG. **13A** and FIG. **13B**.

FIGS. **15A-15E** show a process of forming a cathode electrode according to an example embodiment of the present invention. Other embodiments and configurations are also within the scope of the present invention. More specifically, in the absence of a conductive particle, the first metal layer **241** may be formed on the organic EL layer **230** as shown in FIG. **15A**. FIG. **15B** shows oxide layers **241b** formed adjacent (or on) the first metal layer **241**. FIG. **15C** shows the second metal layer **242** formed on the first metal layer **241** and the oxide layers **241b**.

Additionally, FIG. **15D** shows oxide layers **242b** formed adjacent (or on) the second metal layer **242**. FIG. **15E** shows the third metal layer **243** formed on the second metal layer **242** and the oxide layers **242b**.

Embodiments of the present invention may provide a display device in which a metal electrode is formed with a multi-metal layered structure to prevent (or reduce) generation of leakage current and reduce resistance of the metal electrode. While embodiments have been described with respect to three metal layers, other numbers of metal layers (or conductive layers) are also within the scope of the present invention.

Embodiments of the present invention may provide a method for manufacturing a display device wherein an oxide layer is formed on a periphery area of a conductive particle that may exist in a process of forming a metal electrode. The oxide layer may electrically insulate the conductive particle from the metal layer constituting the metal electrode and may prevent (or reduce) generation of leakage current caused by the conductive particle in the display device. The oxide layer may partially cover the organic EL layer such that the organic EL layer and the metal electrode contact each other at least one area not covered by the oxide layer.

While embodiments of the present invention have been described with respect to conductive particles, other types of particulars and/or materials may also be provided within the display device. Embodiments of the present invention are also applicable to these other particles and/or materials provided in the display device.

The electroluminescent device disclosed in various embodiments may be used in or formed as flexible display for electronic books, newspapers, and magazines, different types of portable devices, e.g., handsets, MP3 players, notebook computers, etc., vehicle audio applications, vehicle navigation applications, televisions, monitors, or other types of devices.

Any reference in this specification to "one embodiment," "an embodiment," "example embodiment," etc., means that a particular feature, structure, or characteristic described in connection with the embodiment is included in at least one embodiment of the present invention. The appearances of such phrases in various places in the specification are not necessarily all referring to the same embodiment. Further, when a particular feature, structure, or characteristic is described in connection with any embodiment, it is submitted that it is within the purview of one skilled in the art to effect

such feature, structure, or characteristic in connection with other ones of the embodiments.

Although embodiments have been described with reference to a number of illustrative embodiments thereof, it should be understood that numerous other modifications and embodiments can be devised by those skilled in the art that will fall within the spirit and scope of the principles of this disclosure. More particularly, various variations and modifications are possible in the component parts and/or arrangements of the subject combination arrangement within the scope of the disclosure, the drawings and the appended claims. In addition to variations and modifications in the component parts and/or arrangements, alternative uses will also be apparent to those skilled in the art.

What is claimed is:

1. An electroluminescent device comprising:

a substrate;

a first electrode provided on the substrate;

a light emitting layer provided on the first electrode;

a second electrode provided on the light emitting layer, the second electrode including a first conductive layer of the electroluminescent device and a second conductive layer of the electroluminescent device on the first conductive layer; and

at least one first insulating layer formed on an upper surface of the first conductive layer of the first electroluminescent device, wherein the at least one first insulating layer includes a plurality of first insulating films spaced apart from one another on the upper surface of the first conductive layer, the plurality of first insulating films provided between the first conductive layer and the second conductive layer of the electroluminescent device, wherein a portion of the upper surface of the first conductive layer of the electroluminescent device is not covered by the plurality of first insulating films of the at least one first insulating layer.

2. The electroluminescent device of claim 1, wherein the at least one first insulating layer is spaced apart from an adjacent first insulating layer by a distance of 1 nm or more.

3. The electroluminescent device of claim 1, wherein the at least one first insulating layer has a width less than the first conductive layer.

4. The electroluminescent device of claim 1, wherein the at least one first insulating layer has a thickness less than the first conductive layer.

5. The electroluminescent device of claim 1, wherein the second conductive layer has a thickness that is the same as or greater than a thickness of the first conductive layer.

6. The electroluminescent device of claim 1, further comprising at least one second insulating layer formed on an upper surface of the second conductive layer.

7. The electroluminescent device of claim 6, wherein the at least one second insulating layer comprises a plurality of second insulating films spaced apart from one another on the upper surface of the second conductive layer of the electroluminescent device.

8. The electroluminescent device of claim 7, wherein the at least one second insulating layer is spaced apart from an adjacent second insulating layer by a distance of 1 nm or more.

9. The electroluminescent device of claim 7, wherein the at least one second insulating layer has a width less than the second conductive layer.

10. The electroluminescent device of claim 1, wherein the second electrode further includes a third conductive layer on the second conductive layer.

13

11. The electroluminescent device of claim 10, wherein the third conductive layer has a thickness that is the same as or greater than the first and second conductive layers.

12. The electroluminescent device of claim 1, wherein the at least one first insulating layer comprises an oxide.

13. The electroluminescent device of claim 1, wherein the first conductive layer comprises a metal layer.

14. A method of forming an electroluminescent device comprising:

forming a first electrode on a substrate;

forming a light emitting layer on the first electrode;

forming a second electrode on the light emitting layer, the second electrode including a first conductive layer and a second conductive layer on the first conductive layer; and

forming at least one first insulating layer, wherein the at least one first insulating layer is formed on an upper surface of the first conductive layer, wherein the at least one first insulating layer includes a plurality of first insulating films spaced apart from one another on the upper surface of the first conductive layer, wherein the plurality of first insulating films is provided between the first conductive layer and the second conductive layer, and

wherein a portion of the upper surface of the first conductive layer is not covered by the plurality of first insulating films of the at least one first insulating layer.

14

15. The method of claim 14, further comprising applying an inverse bias voltage after forming the first conductive layer.

16. The method of claim 14, wherein forming the at least one first insulating layer comprises forming the plurality of first insulating films on the first conductive layer.

17. The method of claim 14, further comprising forming a second insulating layer on an upper surface of the second conductive layer.

18. The method of claim 17, wherein forming the second insulating layer comprises forming a plurality of second insulating films spaced apart from one another on the upper surface of the second conductive layer.

19. The electroluminescent device of claim 1, wherein the first conductive layer has a thickness less than a thickness of the light emitting layer.

20. The electroluminescent device of claim 1, wherein the second electrode has a thickness greater than a thickness of the light emitting layer.

21. The electroluminescent device of claim 6, wherein the at least one second insulating layer has a thickness less than a thickness of the second conductive layer.

22. The electroluminescent device of claim 6, wherein the at least one second insulating layer comprises an oxide.

23. The electroluminescent device of claim 10, wherein the second electrode has a thickness greater than the light emitting layer.

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专利名称(译)	显示装置及其制造方法		
公开(公告)号	US7839086	公开(公告)日	2010-11-23
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摘要(译)

可以提供电致发光器件，其包括基板，设置在基板上的第一电极，设置在第一电极上的发光层，以及设置在发光层上的第一金属层。还可以在第二金属层和导电颗粒的界面处提供氧化物层。还可以提供如本文所述的其他实施例。

